## 16M-BIT MASK-PROGRAMMABLE ROM 2M-WORD BY 8-BIT (BYTE MODE) / 1M-WORD BY 16-BIT (WORD MODE)

## Description

The $\mu$ PD23C16300 is a $16,777,216$ bits mask-programmable ROM. The word organization is selectable (BYTE mode : $2,097,152$ words by 8 bits, WORD mode : $1,048,576$ words by 16 bits).

The active levels of OE (Output Enable Input) can be selected with mask-option.
The $\mu$ PD23C16300 is packed in 48-pin PLASTIC TSOP(I) and 48-pin TAPE FBGA.

## Features

- Pin compatible with NOR Flash Memory
- Word organization

2,097,152 words by 8 bits (BYTE mode)
1,048,576 words by 16 bits (WORD mode)

- Operating supply voltage : Vcc $=2.7 \mathrm{~V}$ to 3.6 V

| Operating supply voltage <br> Vcc | Access time <br> $\mathrm{ns}(\mathrm{MAX})$. | Power supply current (Active mode) <br> $\mathrm{mA}(M A X)$. | Standby current (CMOS level input) |
| :---: | :---: | :---: | :---: |
| $3.0 \mathrm{~V} \pm 0.3 \mathrm{~V}$ | 90 | 30 | 30 |
| $3.3 \mathrm{~V} \pm 0.3 \mathrm{~V}$ | 85 |  |  |

## Ordering Information

| Part Number | Package |
| :--- | :--- |
| $\mu$ PD23C16300GZ-xxx-MJH | 48-pin PLASTIC TSOP $(1)(12 \times 20)$ (Normal bent) |
| $\mu$ PD23C16300F9-xxx-BC3 | 48-pin TAPE FBGA $(8 \times 6)$ |

(xxx : ROM code suffix No.)

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## Pin Configurations

/xxx indicates active low signal.

## 48-pin PLASTIC TSOP(I) (12 x 20) (Normal bent)

## [ $\mu$ PD23C16300GZ-xxx-MJH ]



Note Some signals can be applied because this pin is not connected to the inside of the chip.

Remark Refer to Package Drawings for the 1-pin index mark.

48-pin TAPE FBGA (8 x 6)
[ $\mu$ PD23C16300F9-xxx-BC3]

Top View


Bottom View


|  | A | B | C | D | E | F | G | H |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 6 | A13 | A12 | A14 | A15 | A16 | WORD, <br> /BYTE | O15, <br> A-1 | GND |
| 5 | A9 | A8 | A10 | A11 | O7 | O14 | O13 | O6 |
| 4 | NC | NC | NC | A19 | O5 | O12 | Vcc | O4 |
| 3 | NC | NC | A18 | NC | O2 | O10 | O11 | O3 |
| 2 | A7 | A17 | A6 | A5 | O0 | O8 | O9 | O1 |
| 1 | A3 | A4 | A2 | A1 | A0 | ICE | IOE or | GND |


|  | H | G | F | E | D | C | B | A |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 6 | GND | O15, <br> A-1 | WORD, <br> /BYTE | A16 | A15 | A14 | A12 | A13 |
| 5 | O6 | O13 | O14 | O7 | A11 | A10 | A8 | A9 |
| 4 | O4 | Vcc | O12 | O5 | A19 | NC | NC | NC |
| 3 | O3 | O11 | O10 | O2 | NC | A18 | NC | NC |
| 2 | O1 | O9 | O8 | O0 | A5 | A6 | A17 | A7 |
| 1 | GND | IOE or | ICE | A0 | A1 | A2 | A4 | A3 |


| A0 to A19 | Address inputs |
| :---: | :---: |
| O0 to O7, O8 to O14 | Data outputs |
| O15, A-1 | Data output 15 (WORD mode), <br> LSB Address input (BYTE mode) |
| WORD, /BYTE | Mode select |
| /CE | Chip Enable |
| /OE or OE | Output Enable |
| Vcc | Supply voltage |
| GND | Ground |
| NC ${ }^{\text {Note }}$ | No Connection |
| DC | Don't Care |

Note Some signals can be applied because this pin is not connected to the inside of the chip.
Remark Refer to Package Drawings for the index mark.

## Input / Output Pin Functions

| Pin name | Input / Output | Function |
| :---: | :---: | :---: |
| WORD, /BYTE | Input | The pin for switching WORD mode and BYTE mode. <br> High level : WORD mode (1M-word by 16-bit) <br> Low level : BYTE mode (2M-word by 8-bit) |
| A0 to A19 <br> (Address inputs) | Input | Address input pins. <br> A0 to A19 are used differently in the WORD mode and the BYTE mode. <br> WORD mode (1M-word by 16-bit) <br> A0 to A19 are used as 20 bits address signals. <br> BYTE mode (2M-word by 8-bit) <br> A0 to A19 are used as the upper 20 bits of total 21 bits of address signal. <br> (The least significant bit ( $\mathrm{A}-1$ ) is combined to O 15 .) |
| O0 to O7, O8 to O14 <br> (Data outputs) | Output | Data output pins. <br> O0 to O7, O8 to O14 are used differently in the WORD mode and the BYTE mode. <br> WORD mode (1M-word by 16-bit) <br> The lower 15 bits of 16 bits data outputs to O 0 to O 14 . <br> (The most significant bit (O15) combined to $\mathrm{A}-1$.) <br> BYTE mode (2M-word by 8-bit) <br> 8 bits data outputs to O 0 to O 7 and also O 8 to O 14 are high impedance. |
| O15, A-1 <br> (Data output 15, <br> LSB Address input) | Output, Input | O15, A-1 are used differently in the WORD mode and the BYTE mode. WORD mode (1M-word by 16 -bit) <br> The most significant output data bus (O15). <br> BYTE mode (2M-word by 8-bit) <br> The least significant address bus (A-1). |
| ICE <br> (Chip Enable) | Input | Chip activating signal. <br> When the OE is active, output states are following. <br> High level : High-Z <br> Low level : Data out |
| /OE or OE or DC <br> (Output Enable, Don't care) | Input | Output enable signal. The active level of OE is mask option. The active level of OE can be selected from high active, low active and Don't care at order. |
| Vcc | - | Supply voltage |
| GND | - | Ground |
| NC | - | Not internally connected. (The signal can be connected.) |

## Block Diagram



## Mask Option

The active levels of output enable pin (/OE or OE or DC) are mask programmable and optional, and can be selected from among " 0" " 1 " " x " shown in the table below.

| Option | /OE or OE or DC | OE active level |
| :---: | :---: | :---: |
| 0 | IOE | L |
| 1 | OE | H |
| x | DC | Don't care |

Operation modes for each option are shown in the tables below.

Operation mode (Option : 0)

| /CE | IOE | Mode | Output state |
| :---: | :---: | :---: | :---: |
| L | L | Active | Data out |
|  | H |  | High-Z |
| H | H or L | Standby | High-Z |

Operation mode (Option : 1)

| /CE | OE | Mode | Output state |
| :---: | :---: | :---: | :---: |
| L | L | Active | High-Z |
|  | H |  | Data out |
|  | H | H or L | Standby |

Operation mode (Option : x)

| $/$ CE | DC | Mode | Output state |
| :---: | :---: | :---: | :---: |
| L | H or L | Active | Data out |
| H | H or L | Standby | High-Z |

Remark L: Low level input
$H$ : High level input

## Electrical Specifications

Absolute Maximum Ratings

| Parameter | Symbol | Condition | Rating | Unit |
| :--- | :---: | :---: | :---: | :---: |
| Supply voltage | Vcc |  | -0.3 to +4.6 | V |
| Input voltage | $\mathrm{V}_{\mathrm{l}}$ |  | -0.3 to $\mathrm{Vcc}+0.3$ | V |
| Output voltage | Vo |  | -0.3 to $\mathrm{Vcc}+0.3$ | V |
| Operating ambient temperature | $\mathrm{T}_{\mathrm{A}}$ |  | -10 to +70 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature | $\mathrm{T}_{\text {stg }}$ |  | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |

Caution Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

## Capacitance ( $\mathrm{TA}=25^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Test condition | MIN. | TYP. | MAX. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Input capacitance | Cl | $\mathrm{f}=1 \mathrm{MHz}$ |  |  | 10 | pF |
| Output capacitance | Co |  |  |  | 12 | pF |

DC Characteristics ( $\mathrm{TA}=\mathbf{- 1 0}$ to $\mathbf{+ 7 0}{ }^{\circ} \mathrm{C}$, $\mathrm{Vcc}=\mathbf{2 . 7}$ to $\mathbf{3 . 6} \mathrm{V}$ )

| Parameter | Symbol | Test conditions | MIN. | TYP. | MAX. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| High level input voltage | VIH |  | 2.0 |  | $\mathrm{Vcc}+0.3$ | V |
| Low level input voltage | VIL | $\mathrm{Vcc}=3.0 \mathrm{~V} \pm 0.3 \mathrm{~V}$ | -0.3 |  | +0.5 | V |
|  |  | $\mathrm{Vcc}=3.3 \mathrm{~V} \pm 0.3 \mathrm{~V}$ | -0.3 |  | +0.8 |  |
| High level output voltage | Vor | $\mathrm{IOH}=-100 \mu \mathrm{~A}$ | 2.4 |  |  | V |
| Low level output voltage | Vol | $\mathrm{loL}=2.1 \mathrm{~mA}$ |  |  | 0.4 | V |
| Input leakage current | Iı | $\mathrm{V}_{\mathrm{I}}=0 \mathrm{~V}$ to Vcc | -10 |  | +10 | $\mu \mathrm{A}$ |
| Output leakage current | ILo | V o $=0 \mathrm{~V}$ to Vcc , Chip deselected | -10 |  | +10 | $\mu \mathrm{A}$ |
| Power supply current | Icc1 | $/ \mathrm{CE}=\mathrm{VIL}$ (Active mode), $\mathrm{Io}=0 \mathrm{~mA}$ |  |  | 30 | mA |
| Standby current | Icc3 | $/ \mathrm{CE}=\mathrm{Vcc}-0.2 \mathrm{~V}$ (Standby mode) |  |  | 30 | $\mu \mathrm{A}$ |

## AC Characteristics ( $\mathrm{TA}_{\mathrm{A}}=\mathbf{- 1 0}$ to $+\mathbf{7 0}{ }^{\circ} \mathrm{C}, \mathrm{Vcc}=2.7$ to 3.6 V )

| Parameter | Symbol | Test condition | $\mathrm{Vcc}=3.0 \mathrm{~V} \pm 0.3 \mathrm{~V}$ |  |  | $\mathrm{V} \mathrm{cc}=3.3 \mathrm{~V} \pm 0.3 \mathrm{~V}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |  |
| Address access time | tacc |  |  |  | 90 |  |  | 85 | ns |
| Address skew time | tskew | Note |  |  | 10 |  |  | 10 | ns |
| Chip enable access time | tce |  |  |  | 90 |  |  | 85 | ns |
| Output enable access time | toe |  |  |  | 25 |  |  | 25 | ns |
| Output hold time | tor |  | 0 |  |  | 0 |  |  | ns |
| Output disable time | tbF |  | 0 |  | 25 | 0 |  | 25 | ns |
| WORD, /BYTE access time | tws |  |  |  | 90 |  |  | 85 | ns |

$\star$ Note tskew indicates the following three types of time depending on the condition.

1) When switching /CE from high level to low level, tskEw is the time from the /CE low level input point until the next address is determined.
2) When switching /CE from low level to high level, tskew is the time from the address change start point to the /CE high level input point.
3) When /CE is fixed to low level, tskew is the time from the address change start point until the next address is determined.

Since specs are defined for tskew only when /CE is active, tskEw is not subject to limitations when /CE is switched from high level to low level following address determination, or when the address is changed after /CE is switched from low level to high level.

Remark tDF is the time from inactivation of Chip Enable input (/CE) or Output Enable input (/OE or OE) to high impedance state output.

## AC Test Conditions

Input waveform (Rise / Fall time $\leq \mathbf{5 n s}$ )


## Output waveform



## Output load

1 TTL + 100 pF

## $\star$ Cautions on power application

To ensure normal operation, always apply power using /CE following the procedure shown below.

1) Input a high level to /CE during and after power application.
2) Hold the high level input to /CE for 200 ns or longer (wait time).
3) Start normal operation after the wait time has elapsed.

Power Application Timing Chart 1 (When /CE is made high at power application)


## Power Application Timing Chart 2 (When /CE is made high after power application)



Caution Other signals can be either high or low during the wait time.

## $\star$ Read Cycle Timing Chart



Notes 1. During WORD mode, $\mathrm{A}-1$ is O 15.
2. tDF is the time from inactivation of Chip Enable input (/CE) or Output Enable input (/OE or OE) to high impedance state output.
3. During BYTE mode, O 8 to O 14 are high impedance and O 15 is $\mathrm{A}-1$.

## WORD, IBYTE Switch Timing Chart



Remark Chip Enable (/CE) and Output Enable (/OE or OE) : Active.

## Package Drawings

## 48-PIN PLASTIC TSOP (I) (12x20)



## NOTES

1) Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.
2) "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX.)

| ITEM | MILLIMETERS |
| :---: | :--- |
| A | $12.0 \pm 0.1$ |
| B | 0.45 MAX. |
| C | 0.5 (T.P.) |
| D | $0.22 \pm 0.05$ |
| E | $0.1 \pm 0.05$ |
| F | 1.2 MAX. |
| G | $1.0 \pm 0.05$ |
| I | $18.4 \pm 0.1$ |
| J | $0.8 \pm 0.2$ |
| K | $0.145 \pm 0.05$ |
| L | 0.5 |
| M | 0.10 |
| N | 0.10 |
| P | $20.0 \pm 0.2$ |
| Q | $3^{\circ+5^{\circ}}$ |
| R | 0.25 |
| S | $0.60 \pm 0.15$ |
|  | S48GZ-50-MJH-1 |

## * 48-PIN TAPE FBGA(8x6)



| ITEM | MILLIMETERS |
| :---: | :--- |
| $D$ | $6.0 \pm 0.1$ |
| $E$ | $8.0 \pm 0.1$ |
| $w$ | 0.2 |
| e | 0.80 |
| $A$ | $0.97 \pm 0.10$ |
| A1 | $0.27 \pm 0.05$ |
| A2 | 0.70 |
| $b$ | $0.45 \pm 0.05$ |
| $x$ | 0.08 |
| $y$ | 0.1 |
| $y 1$ | 0.2 |
| $Z D$ | 1.00 |
| $z E$ | 1.20 |
|  | P48F9-80-BC3 |

## Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the $\mu \mathrm{PD} 23 \mathrm{C} 16300$.

Types of Surface Mount Device
$\mu$ PD23C16300GZ-MJH: 48-pin PLASTIC TSOP(I) $(12 \times 20)$ (Normal bent)
$\mu$ PD23C16300F9-BC3 : 48-pin TAPE FBGA $(8 \times 6)$

## Revision History

| Edition/ <br> Date | Page |  | Type of revision | Location | Description <br> (Previous edition $\rightarrow$ This edition) |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  | This edition | Previous edition |  |  |  |
| 2nd edition/ Feb. 2003 | Throughout | Throughout | Modification |  | Preliminary Data Sheet $\rightarrow$ Data Sheet |
|  | p. 8 | p. 8 | Addition | AC Characteristics | Address skew time (tskew) Note |
|  | p. 9 | - | Addition |  | Cautions on power application |
|  | p. 10 | p. 9 | Modification |  | Read Cycle Timing Chart |
|  | p. 12 | p. 11 | Modification | Package Drawings | Preliminary version $\rightarrow$ Standard version |

## NOTES FOR CMOS DEVICES

## (1) PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

## Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.
(2) HANDLING OF THE APPLIED WAVEFORM OF INPUT PINS AND THE UNUSED INPUT PINS FOR CMOS

Note:
Input levels of CMOS devices must be fixed. CMOS devices behave differently than Bipolar or NMOS devices. If the input of a CMOS device stays in an area that is between VIL (MAX.) and $\mathrm{V}_{\mathrm{IH}}$ (MIN.) due to the effects of noise or some other irregularity, malfunction may result. Therefore, not only the input waveform is fixed, but also the waveform changes, it is important to use the CMOS device under AC test conditions. For unused input pins in particular, CMOS devices should not be operated in a state where nothing is connected, so input levels of CMOS devices must be fixed to high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

## (3) STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:
Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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